## AM / FM - PLL

#### Description

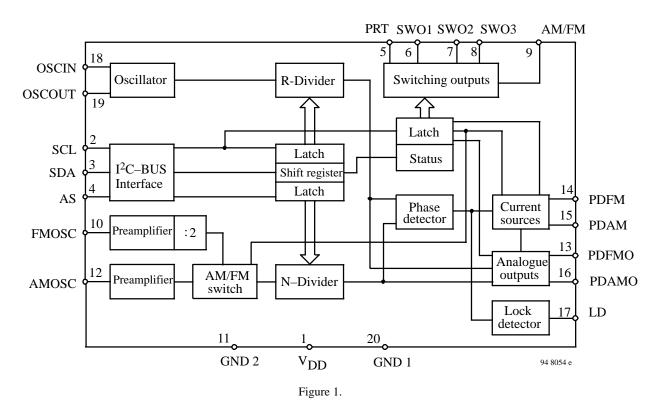
The U4283BM is an integrated circuit in BICMOS technology for frequency synthesizer. It performs all the functions of a PLL radio tuning system and is controlled by  $I^2C$  bus. The device is designed for all frequency syn-

thesizer applications of radio receivers, as well as RDS (Radio Data System) applications.

#### Features

- Reference oscillator up to 15 MHz
- Two programmable 16 bit dividers adjustable from 2 to 65535
- Fine tuning steps:  $AM \ge 1 \text{ kHz}$  $FM \ge 2 \text{ kHz}$

- Three programmable switching outputs (open drain up to 20 V)
- Few external component requirements due to integrated loop-transistor for AM/FM
- High signal/noise ratio

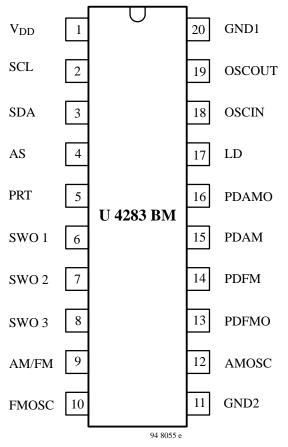


#### **Block Diagram**

## Preliminary Information

# U4283BM

## **Pin Description**



Pin	Symbol	Function
1	V <sub>DD</sub>	Supply voltage
2	SCL	I <sup>2</sup> C bus clock
3	SDA	I <sup>2</sup> C bus data
4	AS	Address selection
5	PRT	Switching port
6	SWO 1	Switching output 1
7	SWO 2	Switching output 2
8	SWO3	Switching output 3
9	AM/FM	Switching output AM/FM
10	FMOSC	FM oscillator input
11	GND 2	Ground 2 (analogue)
12	AMOSC	AM oscillator input
13	PDFMO	FM analogue output
14	PDFM	FM current output
15	PDAM	AM current output
16	PDAMO	AM analogue output
17	LD	Lock detector
18	OSCIN	Oscillator input
19	OSCOUT	Oscillator output
20	GND 1	Ground 1 (digital)

## **Functional Description**

The U4283BM is controlled via the 2-wire I<sup>2</sup>C bus. For programming there are one module address byte, two sub-address bytes and five data bytes.

The module address contains a programmable address bit A 1 which with address select input AS (pin 4) makes it possible to operate two U4283BM-B in one system. If bit A 1 is identical with the status of the address select input AS, the chip is selected.

The subaddress determines which one of the data bytes is transmitted first. If subaddress of R-divider is transmitted, the sequence of the next data bytes is DB 0 (Status), DB 1 and DB 2.

If subaddress of N-divider is transmitted, the sequence of the next data bytes is DB 3 and DB 4. The bit organisation of the module address, subaddress and 5 data bytes are shown in figure 2. Each transmission on the  $I^2C$  bus begins with the "START"-condition and has to be ended by the "STOP"-condition (see figure 3.).

The integrated Circuit U 4283 BM has two separate inputs for AM and FM oscillator. Pre-amplified AM signal is directed to the 16 bit N-divider via AM/FM switch, whereas (pre-amplified) FM signal is first divided by a fixed prescaler (:2). AM/FM switch is controlled by software. Tuning steps can be selected by 16 bit R-divider. Further there is a digital memory phase detector. There are two separate current sources for AM and FM amplifier (charge pump) as given in electrical characteristics. It allows independent adjustment of gain, whereby providing high current for high speed tuning and low current for stable tuning.

## **Bit Organisation**

		-	1			1	1	1
	MSB							LSB
Module address	1	1	0	0	1	0	0/1	0
	A7	A6	A5	A4	A3	A2	A1	A0
~						1		
Subaddress (R-divider)	X	X	X	Х	0	1	X	X
Subaddress (N-divider)	X	X	X	X	1	1	X	X
			1			1		1
	MSB							LSE
Data byte 0 (Status)	PRT	SWO1	SWO2	SWO3	AM/	PD	PD	PD
	D7	D6	D5	D4	FM D3	ANA D2	POL D1	CUF D0
	D/	D0	D3	D4	D3	D2	DI	
Data byte 1	2 <sup>15</sup>			R-div	vider			28
Duu ojto 1				it ui				
Data byte 2	27			R-div	vider			20
								-
Data byte 3	215			N-div	vider			28
Data byte 4	2 <sup>7</sup> N-divider						20	

	LOW	HIGH
AM/FM	FM-operation	AM-operation
PD – ANA	PD analogue	TEST
PD – POL	Negative polarity	Positive polarity
PD – CUR	Output current 2	Output current 1

Figure 2.

#### **Transmission Protocol**

	MSB	LSB										
S	Add	ress	A	Subaddress	А	Data 0	А	Data 1	А	Data 2	А	Р
	A7	A0		R-divider								

	MSB	LSB								
S	Add		А	Subaddress	А	Data 3	А	Data 4	A	Р
	A7	A0		N-divider				А		

S = Start P = Stop A = Acknowledge

Figure 3.

## **Absolute Maximum Ratings**

Parameters	Symbol	Value	Unit
Supply voltage Pin 1	V <sub>DD</sub>	-0.3 to +6	V
Input voltage Pins 2, 3, 4, 10, 12, 18, 19	VI	-0.3 to V <sub>DD</sub> $+0.3$	V
Output current Pins 3, 5, 6, 7, 8, 9	IO	-1 to +5	mA
Output drain voltage Pins 6, 7, 8, 9	V <sub>OD</sub>	20	V
Output voltage Pins 13, 16	V <sub>AO</sub>	15	V
Output current Pins 13, 16	I <sub>AO</sub>	-1 to +20	mA
Ambient temperature range	T <sub>amb</sub>	-25 to +85	°C
Storage temperature range	T <sub>stg</sub>	-40 to +125	°C
Junction temperature	T <sub>i</sub>	125	°C
Electrostatic handling (MIL Standard 883C)	$\pm V_{ESD}$	2000	V

#### **Thermal Resistance**

Parameters	Symbol	Value	Unit
Junction ambient	R <sub>thJA</sub>	160	K/W

## **Electrical Characteristics**

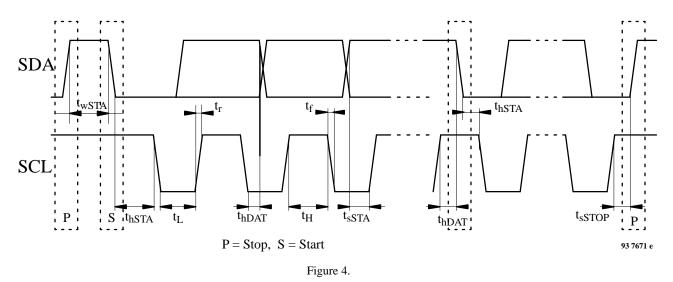
 $V_{DD} = 5$  V,  $T_{amb} = 25^{\circ}$ C, unless otherwise specified.

Parameters	Test Conditions / Pi	ns	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	Pi	n 1	V <sub>DD</sub>	4.5	5.0	5.5	V
Quiescent		n 1					
supply current			I <sub>DD</sub>		6.0	11.6	mA
<b>FM</b> Input Sensitivity, $R_G = 1$	50Ω FMOSC						
$f_i = 70 \text{ to } 120 \text{ MHz}$		n 10	V <sub>SFM</sub>	25			mV
$f_i = 120$ to 130 MHz	Pi	n 10	V <sub>SFM</sub>	50			mV
AM Input Sensitivity, R <sub>G</sub> =	50 Ω AMOSC		01111				
$f_i = 0.5 \text{ to } 35 \text{ MHz}$		n 12	V <sub>SAM</sub>	25			mV
Oscillator Input Sensitivity,	$R_{G} = 50 \Omega OSCIN$		bi iiii	II			
$f_i = 0.1$ to 15 MHz		n 14	V <sub>SOSC</sub>	100			mV
Switching Output SWO 1, S	WO 2, SWO3, AM/FN	I (Ope		II			
Output voltage	Pins 6, 7.	_	,				
LOW	$I_L = 1 \text{ mA}$	, , ,	V <sub>SWOL</sub>		200	400	mV
LOW	$I_{L} = 0.1 \text{ mA}$		V <sub>SWOL</sub>		20	100	mV
Output leakage current	Pins 6, 7	, 8, 9					
HIGH	V5, V6 = 20 V		I <sub>OHL</sub>			100	nA
Lock detector output (Open	Drain)			1			
Output voltage							
LOW	I = 3 mA					0.4	V
Switching output PRT	Pin 5						
Output voltage							
HIGH	$I_L = 1 \text{ mA}$		V <sub>OH</sub>	$V_{DD}$ –0.4		0.4	V
LOW LOW	$I_L = 1 \text{ mA}$		V <sub>OL</sub>			0.4 0.1	V V
	$I_L = 0.1 \text{ mA}$		V <sub>OL</sub>			0.1	v
Phase Detector PDFM		14		400	500	(00	
Output current 1 Output current 2		n 14	$\pm I_{PDFM}$	400 100	500 125	600 150	μA
· · ·	PI PI	n 14	$\pm I_{PDFM}$	100	123	130	μΑ
Phase Detector PDAM	D'	. 15	1 <b>T</b>	75	100	105	
Output current 1 Output current 2		n 15 n 15	$\pm I_{PDAM}$	75 20	100 25	125 30	μΑ μΑ
Analogue Output PDFMO,		1115	$\pm I_{PDAM}$	20	23	30	μΑ
Saturation voltage	I = 15 mA Pins 13,	16	V		270	400	mV
Laakaga gurrant	Pins 13,		V <sub>sat</sub>		270		
Leakage current I <sup>2</sup> C Bus SCL, SDA, AS	Fills 15,	10	I <sub>LEAK</sub>			1	μΑ
	D: 0.2	4	X.Z				
Input voltage HIGH	Pin 2, 3,	4	V <sub>iBUS</sub>	2.0		<b>V</b>	v
LOW				3.0 0		V <sub>DD</sub>	v V
Output voltage	$I_{SDA} = 3 \text{ mA}$ Pi	n 3				1.5	v
Acknowledge LOW	1SDA - 5 mA   FI	.11.5	Vo			0.4	v
Clock frequency	Di	n 2	f <sub>SCL</sub>			100	kHz
Rise time SDA, SCL	Pin 2, 3		t <sub>r</sub>			1	μs

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Parameters	Test Conditions / Pins	Symbol	Min.	Тур.	Max.	Unit
Fall time SDA, SCL	Pin 2, 3	t <sub>f</sub>			300	ns
Period of SCL	Pin 2					
HIGH		t <sub>H</sub>	4.0			μs
LOW		tL	4.7			μs
Setup Time						
Start condition		t <sub>sSTA</sub>	4.7			μs
Data		t <sub>sDAT</sub>	250			ns
Stop condition		t <sub>sSTOP</sub>	4.7			μs
Time the bus must be free						
before a new transmission		t <sub>wSTA</sub>	4.7			μs
can be started						
Hold time						
Start condition		t <sub>hSTA</sub>	4.0			μs
DATA		t <sub>hDAT</sub>	0			μs

## **Bus Timing**





- C<sub>3</sub> = 100 nF should be very close to pin 1 (V<sub>DD</sub>) and Pin 20 (GND 1)
- GND 2 (Pin 10 analogue ground) and GND 1 (Pin 20 digital ground ) must be connected according to figure 6.
- 4 MHz quartz must be very close to Pin 18 and Pin 19
- Components of the charge pump (C<sub>1</sub>/R<sub>1</sub> for AM and C<sub>2</sub>/R<sub>2</sub> for FM) should be very close to Pin 15 with respect to Pin 14.

## **Application Circuit**

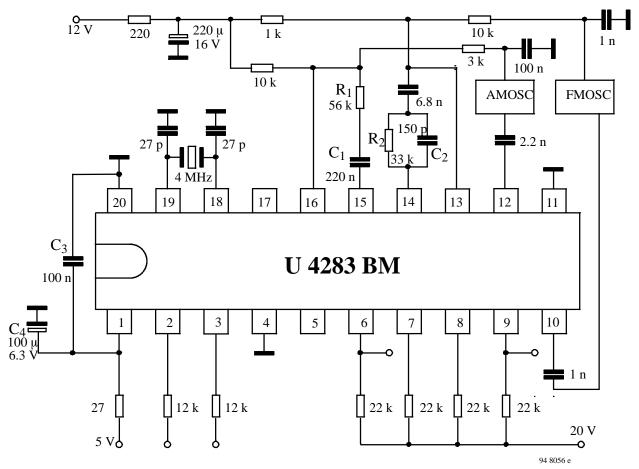
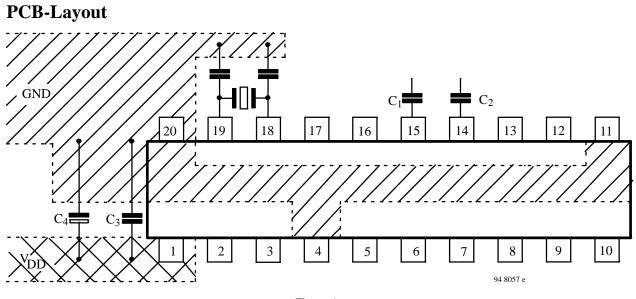


Figure 5.



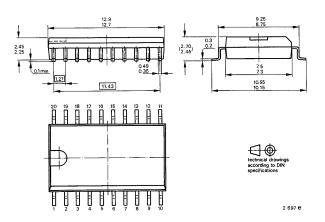


#### **Ordering and Package Information**

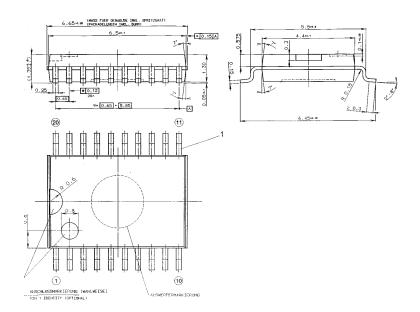
Extended Type Number	Package	Remarks
U4283BM-BFP	SO 20 plastic	
U4283BM-BFPG3	SO 20 plastic	Taping according to IEC–286–3
U4283BM-BFS	SSO 20 plastic	

#### **Dimensions in mm**

Package: SO 20



Package: SSO 20



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It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC TELEFUNKEN microelectronic GmbH** semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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**Preliminary Information**